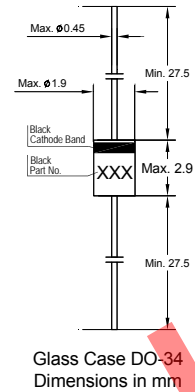


1SS176

Silicon Epitaxial Planar Switching Diode

Applications

- High-speed switching

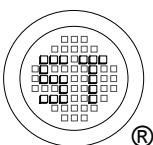


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Peak Reverse Voltage	V_{RM}	35	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Forward Voltage	V_F	300	mV
Surge Forward Current at $t = 1\text{ s}$	I_{FSM}	1	A
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 30\text{ V}$	I_R	0.5	μA
Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	3	pF
Reverse Recovery Time at $I_F = 100\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$	t_{rr}	4	ns



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